MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

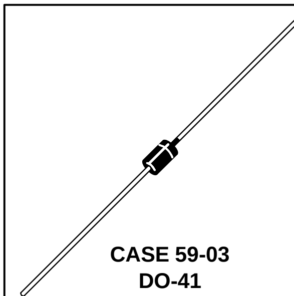
BZX85C3V3RL SERIES
1–1.3 WATT DO-41 GLASS

1–1.3 Watt DO-41 Glass
Zener Voltage Regulator Diodes

GENERAL DATA APPLICABLE TO ALL SERIES IN THIS GROUP

One Watt Hermetically Sealed Glass Silicon Zener Diodes

1 WATT **ZENER REGULATOR** **DIODES** **3.3–100 VOLTS**



CASE 59-03
DO-41
GLASS

Specification Features:
- Complete Voltage Range — 3.3 to 100 Volts
- DO-41 Package
- Double Slug Type Construction
- Metallurgically Bonded Construction
- Oxide Passivated Die

Mechanical Characteristics:

CASE: Double slug type, hermetically sealed glass
MAXIMUM LEAD TEMPERATURE FOR SOLDERING PURPOSES: 230°C, 1/16″ from case for 10 seconds
FINISH: All external surfaces are corrosion resistant with readily solderable leads
POLARITY: Cathode indicated by color band. When operated in zener mode, cathode will be positive with respect to anode
MOUNTING POSITION: Any
WAFER FAB LOCATION: Phoenix, Arizona
ASSEMBLY/TEST LOCATION: Seoul, Korea

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
DC Power Dissipation @ T_A = 50°C Derate above 50°C	P_D	1 6.67	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	– 65 to +200	°C

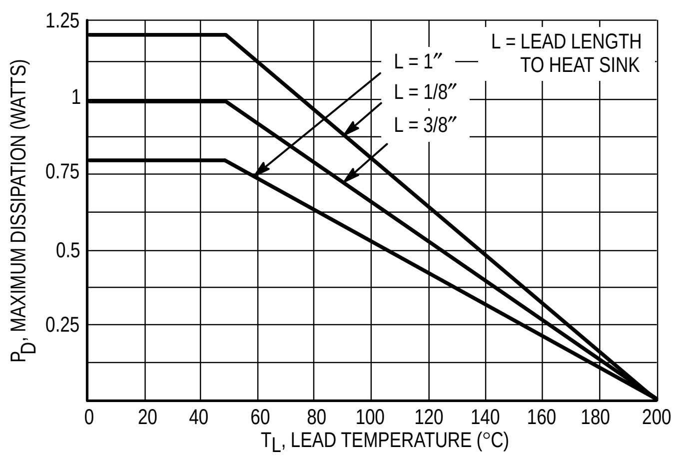


Figure 1. Power Temperature Derating Curve

GENERAL DATA — 500 mW DO-35 GLASS

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.) (V_F = 1.2 V Max, I_F = 200 mA for all types.)

Type (Note 1)	Zener Voltage V_{ZT} (V) (Notes 2 and 3)		Test Current I_{ZT} (mA)	Zener Impedance Z_Z (ohms) (Note 4)			Leakage Current (μA)		Surge Current T_A = 25°C i_r (mA) (Note 5)
	V_Z Min	V_Z Max		Max at I_{ZT}	Max at I_Z	(mA)	V_R (V)	I_R Max	
BZX85C3V3RL	3.1	3.5	80	20	400	1	1	60	1380
BZX85C3V6RL	3.4	3.8	60	15	500	1	1	30	1260
BZX85C3V9RL	3.7	4.1	60	15	500	1	1	5	1190
BZX85C4V3RL	4	4.6	50	13	500	1	1	3	1070
BZX85C4V7RL	4.4	5	45	13	600	1	1.5	3	970
BZX85C5V1RL	4.8	5.4	45	10	500	1	2	1	890
BZX85C5V6RL	5.2	6	45	7	400	1	2	1	810
BZX85C6V2RL	5.8	6.6	35	4	300	1	3	1	730
BZX85C6V8RL	6.4	7.2	35	3.5	300	1	4	1	660
BZX85C7V5RL	7	7.9	35	3	200	0.5	4.5	1	605
BZX85C8V2RL	7.7	8.7	25	5	200	0.5	5	1	550
BZX85C9V1RL	8.5	9.6	25	5	200	0.5	6.5	1	500
BZX85C10RL	9.4	10.6	25	7	200	0.5	7	0.5	454
BZX85C12RL	11.4	12.7	20	9	350	0.5	8.4	0.5	380
BZX85C13RL	12.4	14.1	20	10	400	0.5	9.1	0.5	344
BZX85C15RL	13.8	15.6	15	15	500	0.5	10.5	0.5	304
BZX85C16RL	15.3	17.1	15	15	500	0.5	11	0.5	285
BZX85C18RL	16.8	19.1	15	20	500	0.5	12.5	0.5	250
BZX85C22RL	20.8	23.3	10	25	600	0.5	15.5	0.5	205
BZX85C24RL	22.8	25.6	10	25	600	0.5	17	0.5	190
BZX85C27RL	25.1	28.9	8	30	750	0.25	19	0.5	170
BZX85C30RL	28	32	8	30	1000	0.25	21	0.5	150
BZX85C33RL	31	35	8	35	1000	0.25	23	0.5	135
BZX85C36RL	34	38	8	40	1000	0.25	25	0.5	125
BZX85C43RL	40	46	6	50	1000	0.25	30	0.5	110
BZX85C47RL	44	50	4	90	1500	0.25	33	0.5	95
BZX85C56RL	52	60	4	120	2000	0.25	39	0.5	80
BZX85C62RL	58	66	4	125	2000	0.25	43	0.5	70
BZX85C75RL	70	80	4	150	2000	0.25	51	0.5	60
BZX85C82RL	77	87	2.7	200	3000	0.25	56	0.5	55
BZX85C100RL	96	106	2.7	350	3000	0.25	68	0.5	45

NOTE 1. TOLERANCE AND TYPE NUMBER DESIGNATION

The type numbers listed have zener voltage min/max limits as shown. Device tolerance of ±2% are indicated by a “B” instead of “C.”

NOTE 2. SPECIALS AVAILABLE INCLUDE:

Nominal zener voltages between the voltages shown and tighter voltage tolerances.

For detailed information on price, availability, and delivery, contact your nearest Motorola representative.

NOTE 3. ZENER VOLTAGE (V_Z) MEASUREMENT

V_Z is measured after the test current has been applied to 40 ± 10 msec., while maintaining the lead temperature (T_L) at 30°C ± 1°C, 3/8″ from the diode body.

NOTE 4. ZENER IMPEDANCE (Z_Z) DERIVATION

The zener impedance is derived from the 1 kHz cycle ac voltage, which results when an ac current having an rms value equal to 10% of the dc zener current (I_{ZT}) or (I_{ZK}) is superimposed on I_{ZT} or I_{ZK}.

NOTE 5. SURGE CURRENT (i_r) NON-REPETITIVE

The rating listed in the electrical characteristics table is maximum peak, non-repetitive, reverse surge current of 1/2 square wave or equivalent sine wave pulse of 1/120 second duration superimposed on the test current I_{ZT}. However, actual device capability is as described in Figure 5 of General Data DO-41 glass.

a. Range for Units to 12 Volts **b. Range for Units to 12 to 100 Volts**

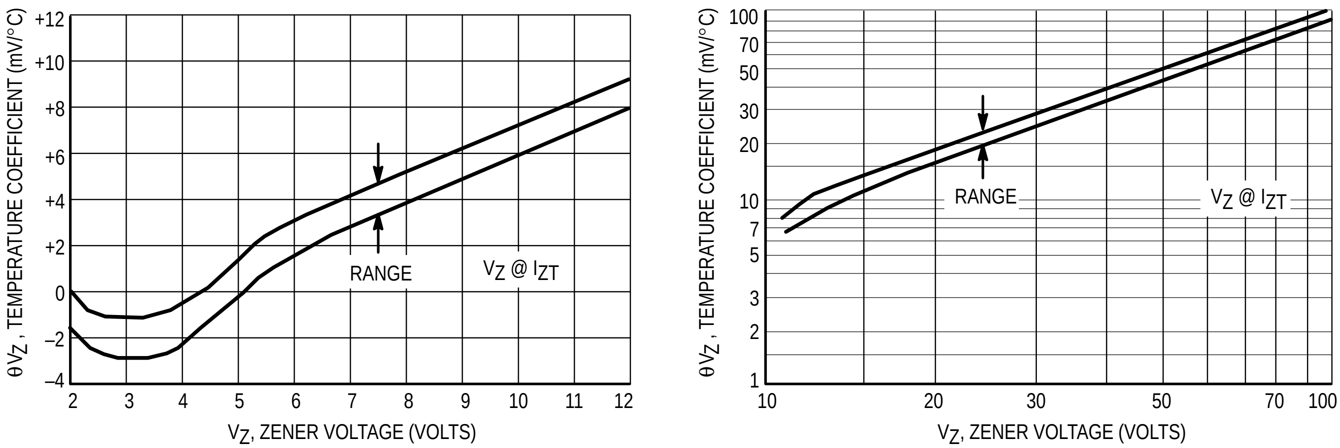


Figure 2. Temperature Coefficients

(–55°C to +150°C temperature range; 90% of the units are in the ranges indicated.)

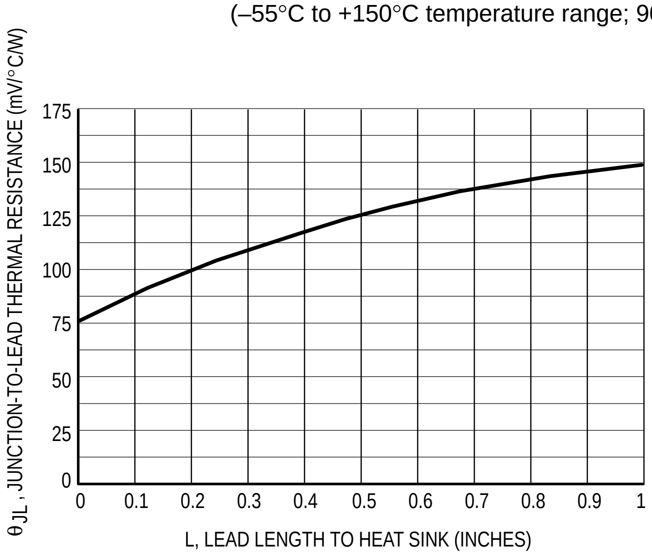


Figure 3. Typical Thermal Resistance versus Lead Length

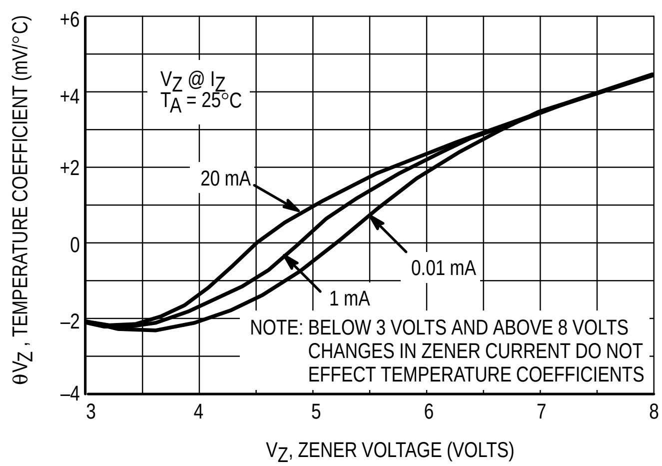
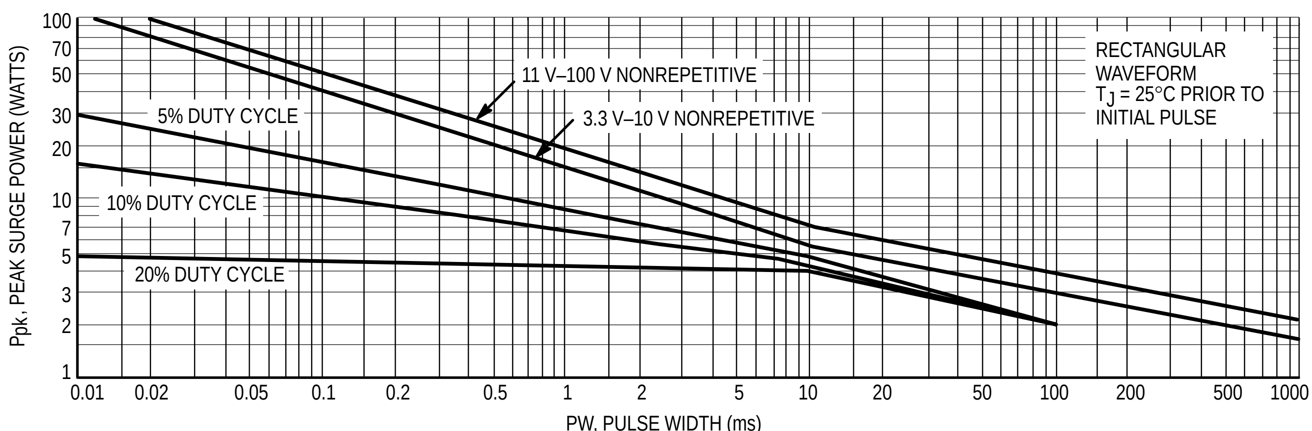


Figure 4. Effect of Zener Current



This graph represents 90 percentile data points.
For worst case design characteristics, multiply surge power by 2/3.

Figure 5. Maximum Surge Power

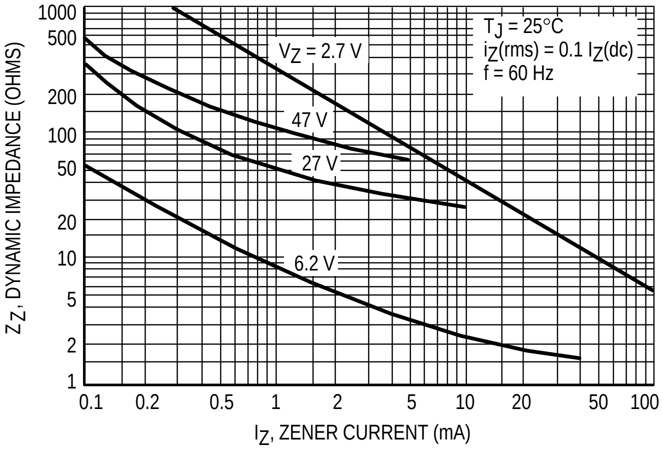


Figure 6. Effect of Zener Current on Zener Impedance

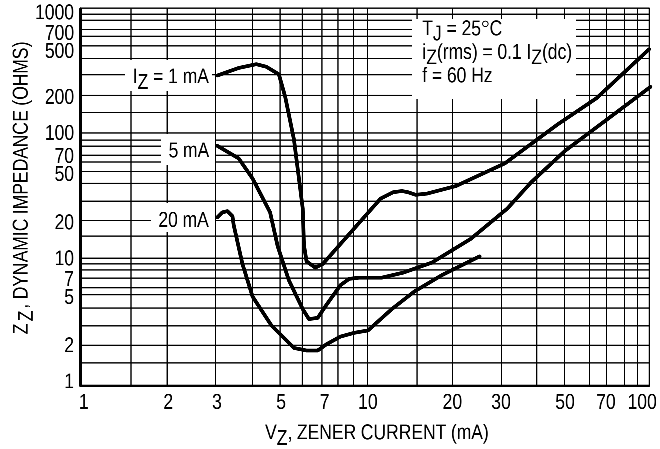


Figure 7. Effect of Zener Voltage on Zener Impedance

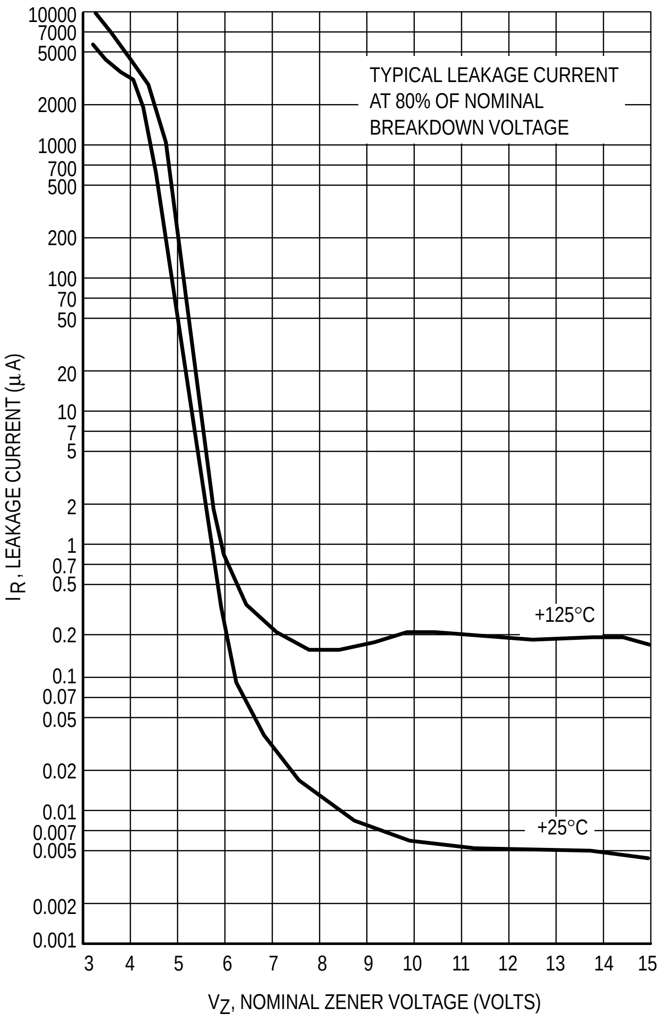


Figure 8. Typical Leakage Current

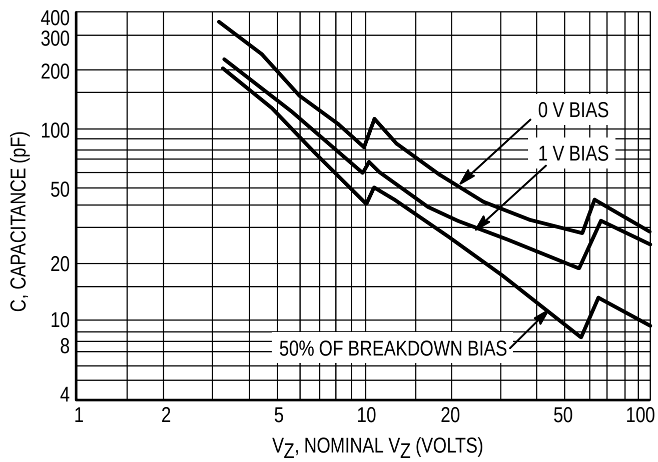


Figure 9. Typical Capacitance versus V_Z

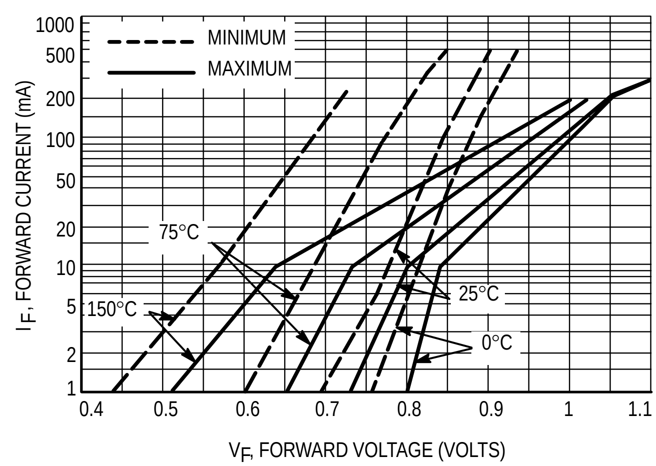


Figure 10. Typical Forward Characteristics

APPLICATION NOTE

Since the actual voltage available from a given zener diode is temperature dependent, it is necessary to determine junction temperature under any set of operating conditions in order to calculate its value. The following procedure is recommended:

Lead Temperature, T_L, should be determined from:

$$T_L = \theta_{LA} P_D + T_A.$$

θ_{LA} is the lead-to-ambient thermal resistance (°C/W) and P_D is the power dissipation. The value for θ_{LA} will vary and depends on the device mounting method. θ_{LA} is generally 30 to 40°C/W for the various clips and tie points in common use and for printed circuit board wiring.

The temperature of the lead can also be measured using a thermocouple placed on the lead as close as possible to the tie point. The thermal mass connected to the tie point is normally large enough so that it will not significantly respond to heat surges generated in the diode as a result of pulsed operation once steady-state conditions are achieved. Using the measured value of T_L, the junction temperature may be determined by:

$$T_J = T_L + \Delta T_{JL}.$$

ΔT_{JL} is the increase in junction temperature above the lead temperature and may be found as follows:

$$\Delta T_{JL} = \theta_{JL} P_D.$$

θ_{JL} may be determined from Figure 3 for dc power conditions. For worst-case design, using expected limits of I_Z, limits of P_D and the extremes of $T_J (\Delta T_J)$ may be estimated. Changes in voltage, V_Z, can then be found from:

$$\Delta V = \theta_{VZ} \, \Delta T_J.$$

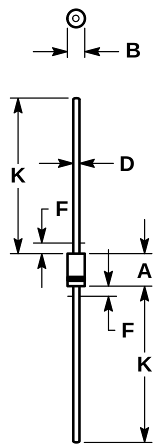
θ_{VZ}, the zener voltage temperature coefficient, is found from Figure 2.

Under high power-pulse operation, the zener voltage will vary with time and may also be affected significantly by the zener resistance. For best regulation, keep current excursions as low as possible.

Surge limitations are given in Figure 5. They are lower than would be expected by considering only junction temperature, as current crowding effects cause temperatures to be extremely high in small spots, resulting in device degradation should the limits of Figure 5 be exceeded.

Zener Voltage Regulator Diodes — Axial Leaded

1–1.3 Watt DO-41 Glass



NOTES:
1. ALL RULES AND NOTES ASSOCIATED WITH JEDEC DO-41 OUTLINE SHALL APPLY.
2. POLARITY DENOTED BY CATHODE BAND.
3. LEAD DIAMETER NOT CONTROLLED WITHIN F DIMENSION.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	4.07	5.20	0.160	0.205
B	2.04	2.71	0.080	0.107
D	0.71	0.86	0.028	0.034
F	—	1.27	—	0.050
K	27.94	—	1.100	—

CASE 59-03
DO-41
GLASS

(Refer to Section 10 for Surface Mount, Thermal Data and Footprint Information.)

MULTIPLE PACKAGE QUANTITY (MPQ) REQUIREMENTS

Package Option	Type No. Suffix	MPQ (Units)
Tape and Reel	RL, RL2	6K
Tape and Ammo	TA, TA2	4K

NOTE: 1. The “2” suffix refers to 26 mm tape spacing.

(Refer to Section 10 for more information on Packaging Specifications.)